

Epitaxial Cu film: an ideal platform for the graphene growth, transfer and device fabrication

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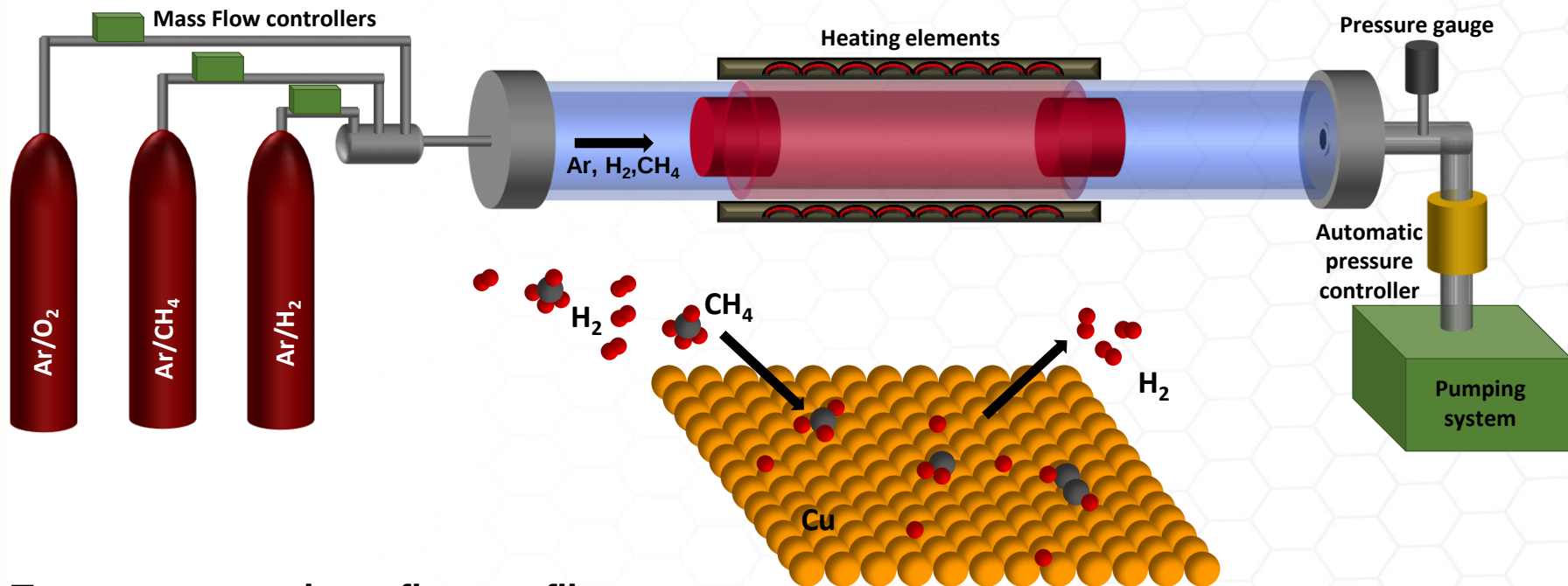
⁴ *Department of Materials Science and Engineering, The Pennsylvania State University, PA 16802, USA*

Monday July 29, 17:15-17:30

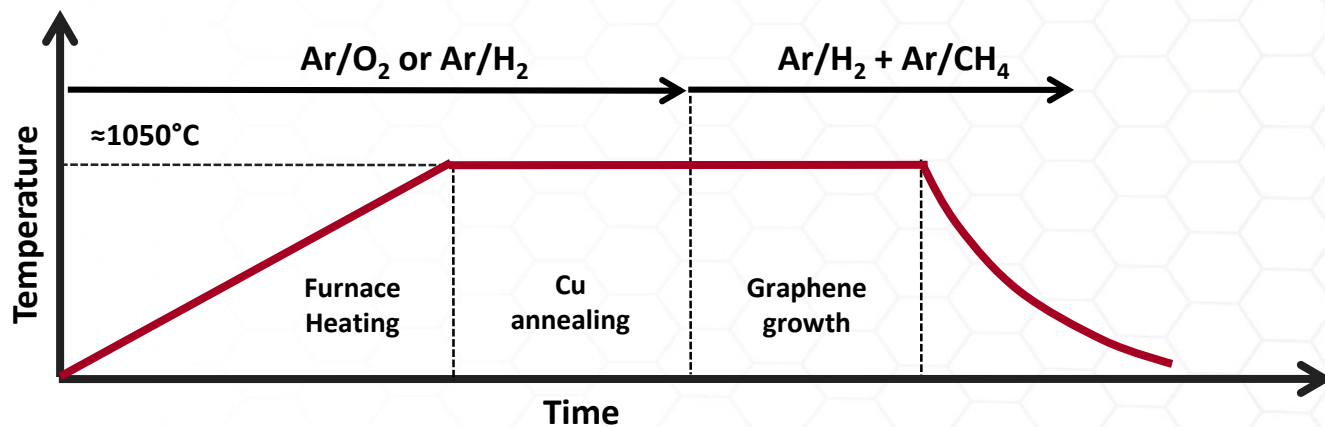




- 1. Introduction**
- 2. Cu substrate roughness & graphene planarity**
- 3. As-grown graphene physical integrity**
- 4. Control over the thickness**
- 5. Transfer of graphene**
- 6. Direct characterization and device fabrication**
- 7. Conclusions**

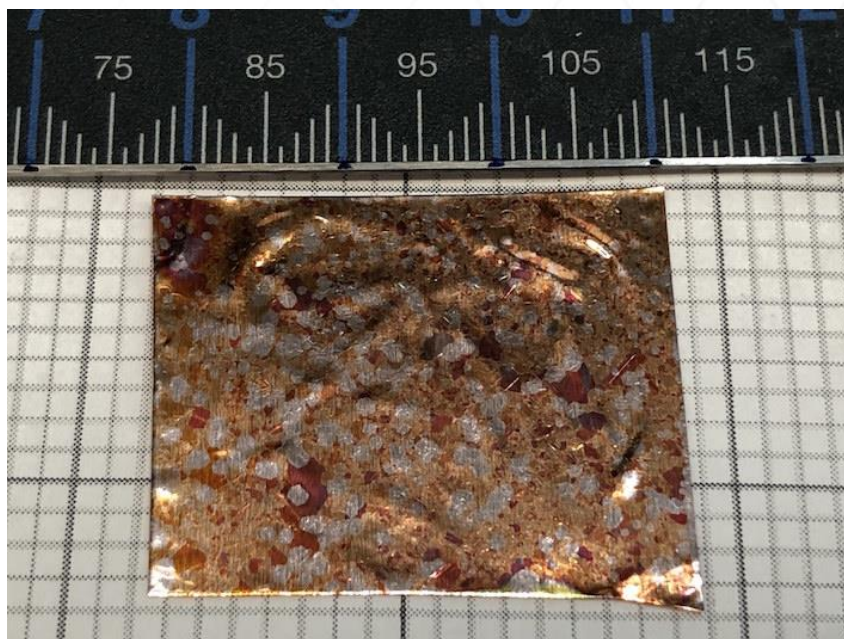
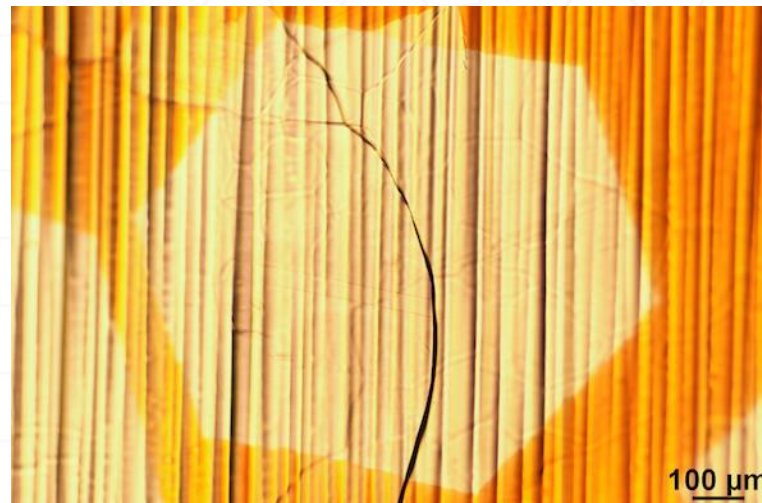
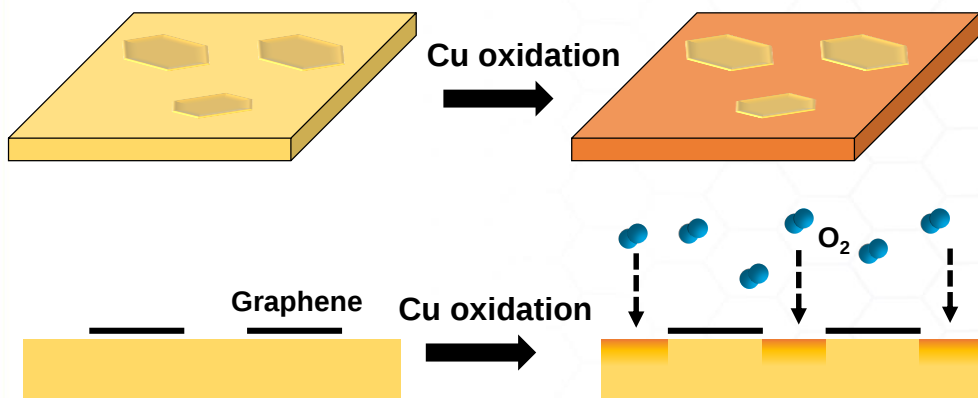


Temperature and gas flow profile





Direct optical visualization of graphene

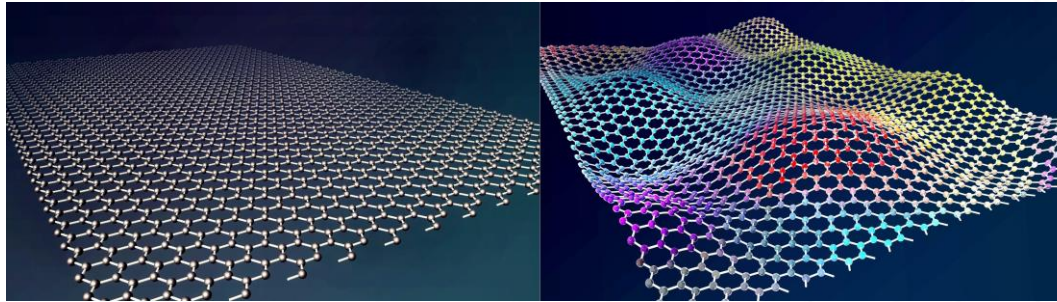




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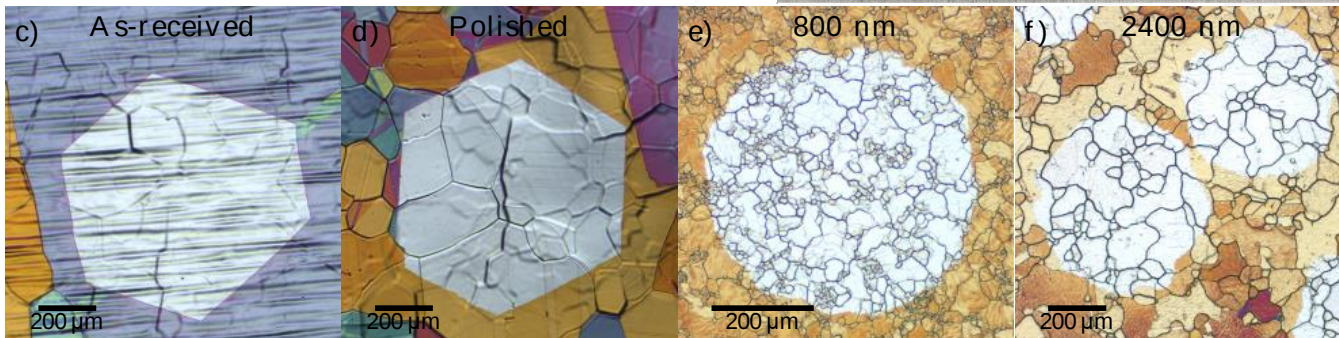
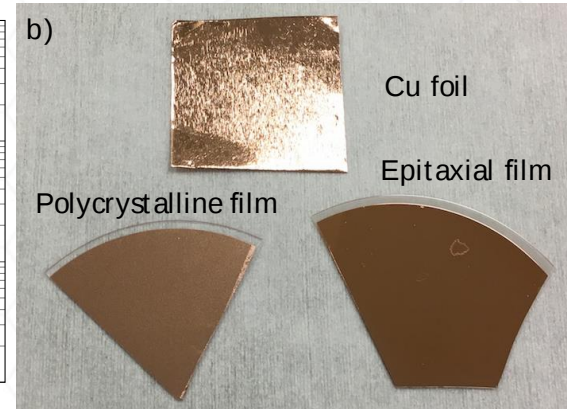
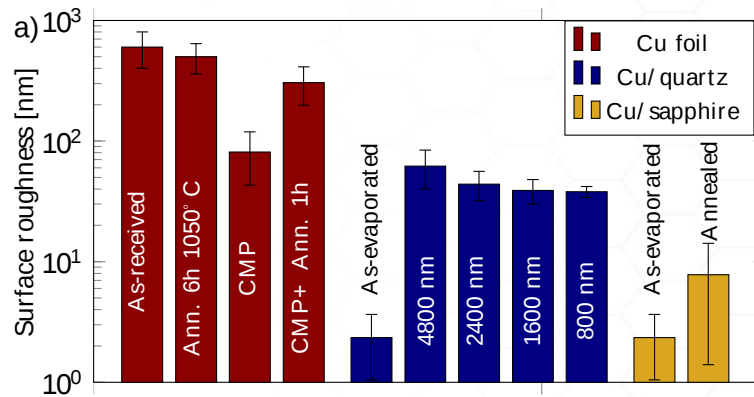


Surface planarity: foils vs. films



[Harvard University, 2011]

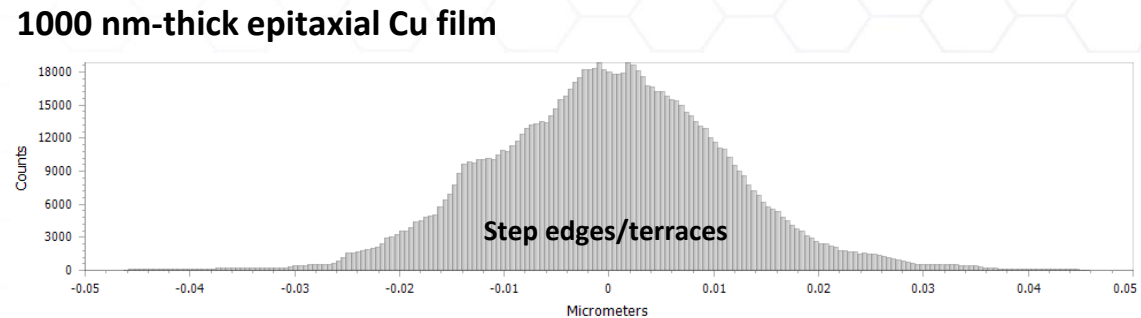
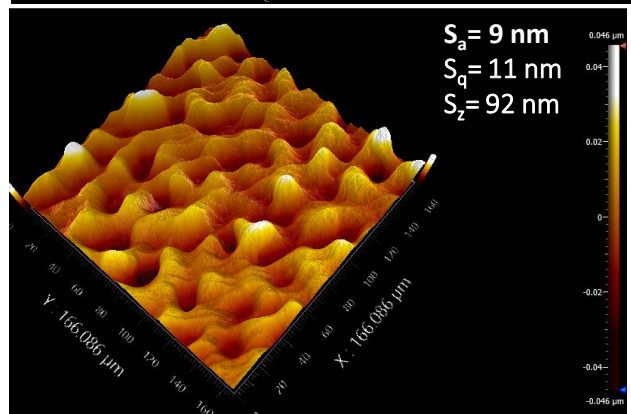
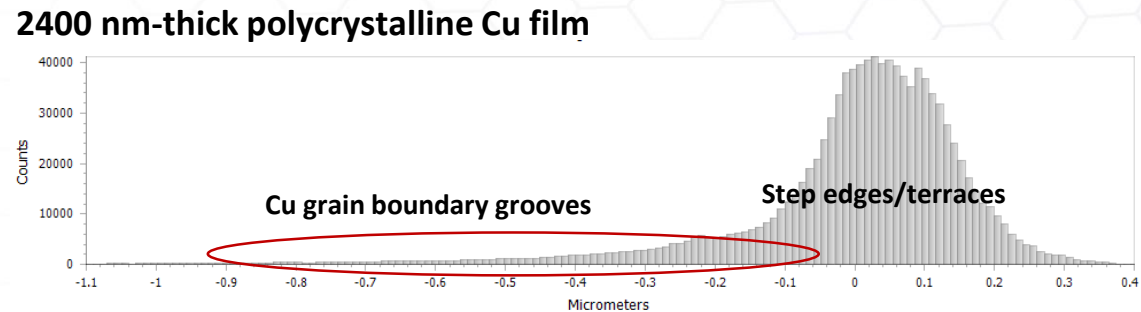
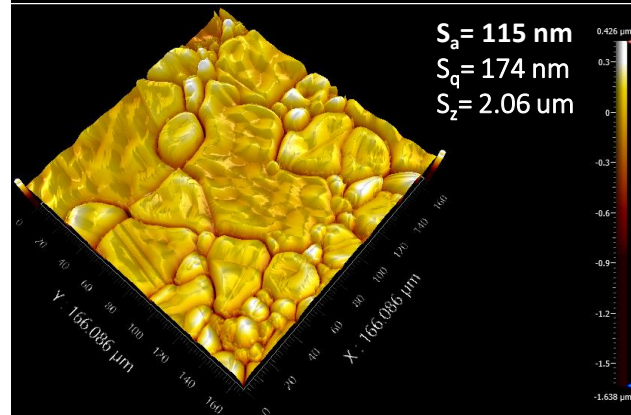
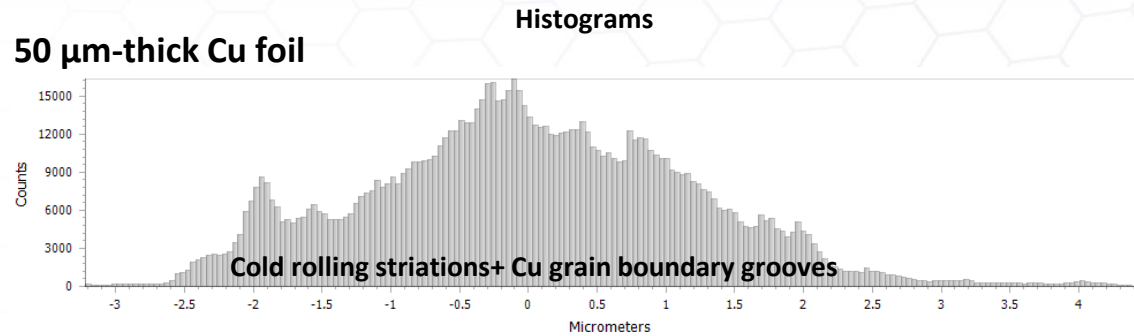
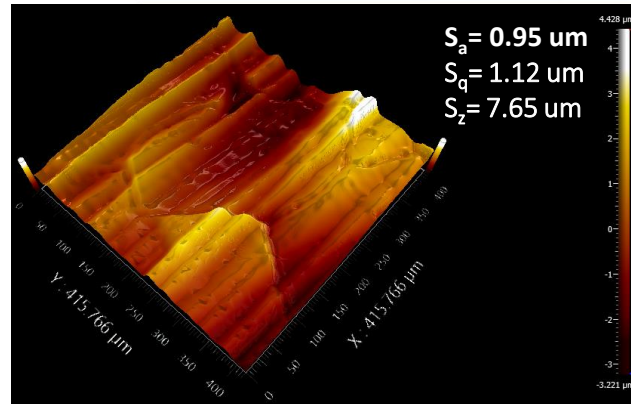
Graphene growth mimics Cu substrate surface morphology!



[B. Huet et al., Nanoscale (10) 21898, 2018]

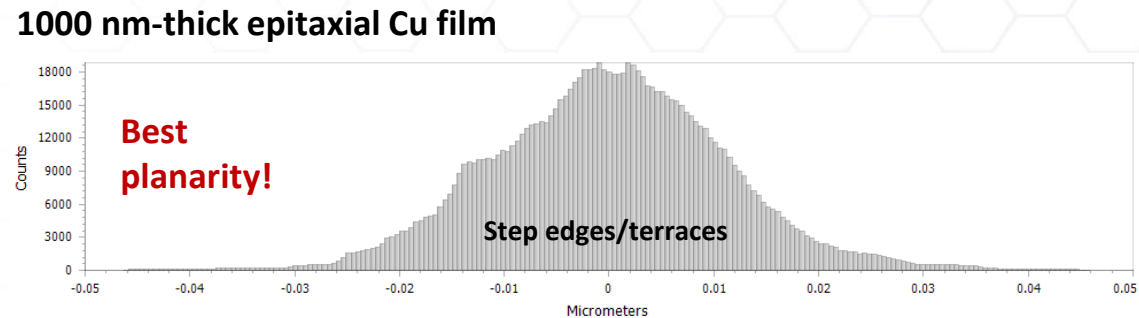
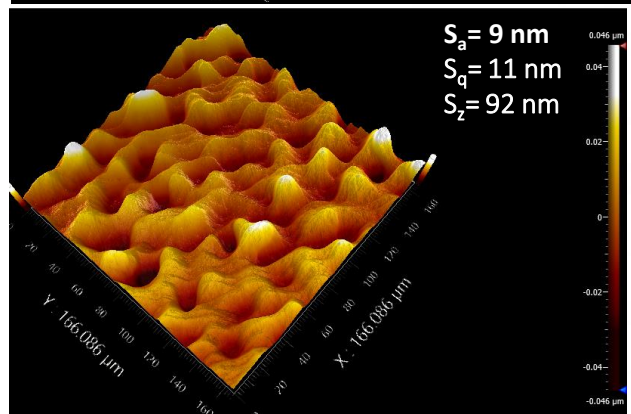
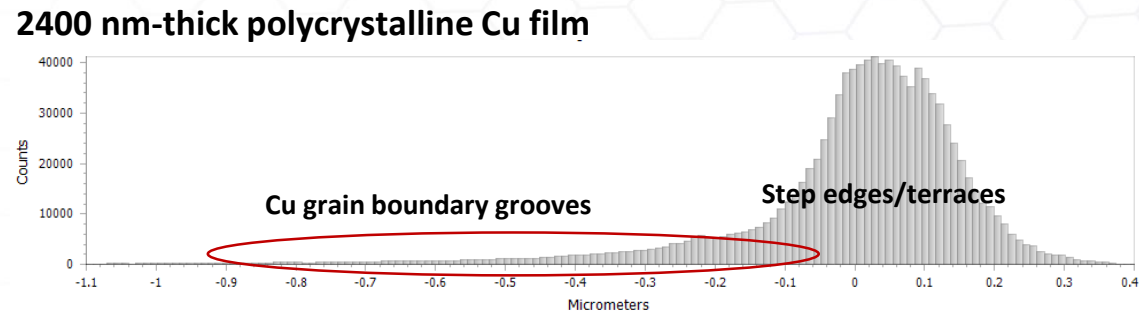
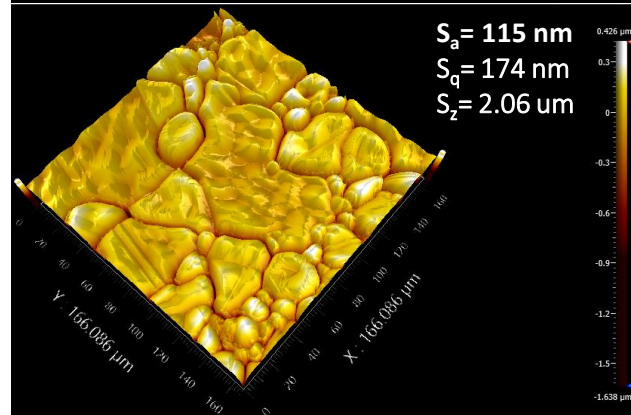
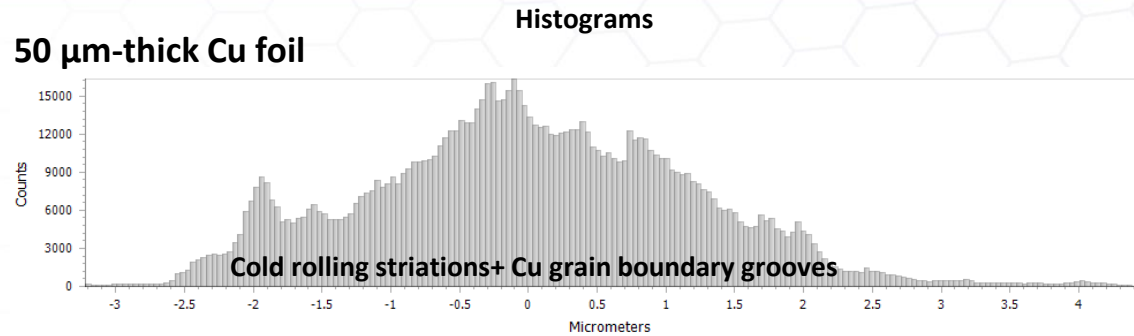
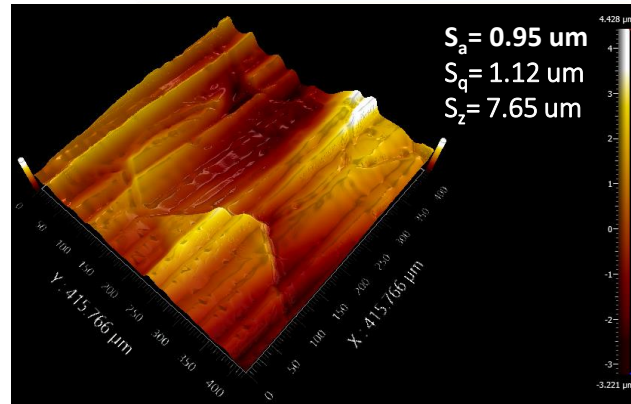


Cu surface benchmarking





Cu surface benchmarking



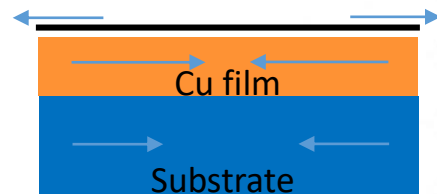


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In-plane compressive strain building up during cooling:

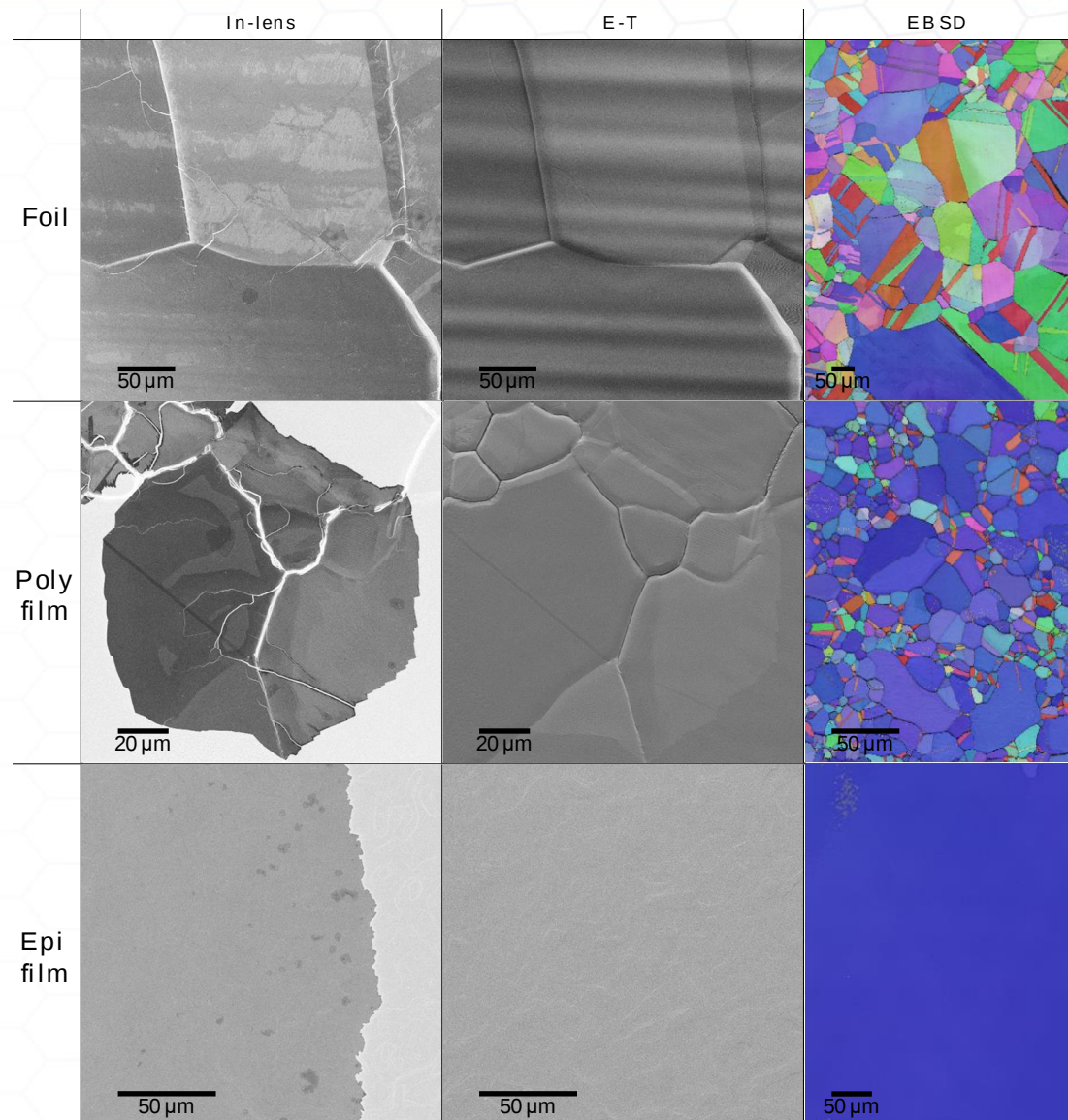
$$\epsilon \approx \Delta T (\alpha_{gr} - \alpha_{\text{Substrate}})$$

$$\Delta T = 1050^{\circ}\text{C} - 20^{\circ}\text{C}$$



Thermal expansion coefficient:

- Graphene: -8.0 to -1.0 ($\times 10^{-6}/\text{K}$)
- Copper: $+16.7$ to $+19.8$ ($\times 10^{-6}/\text{K}$)
- Fused quartz: $+4.0$ to $+6.0$ ($\times 10^{-6}/\text{K}$)
- C-plane sapphire: $+6.6$ to $+9.0$ ($\times 10^{-6}/\text{K}$)



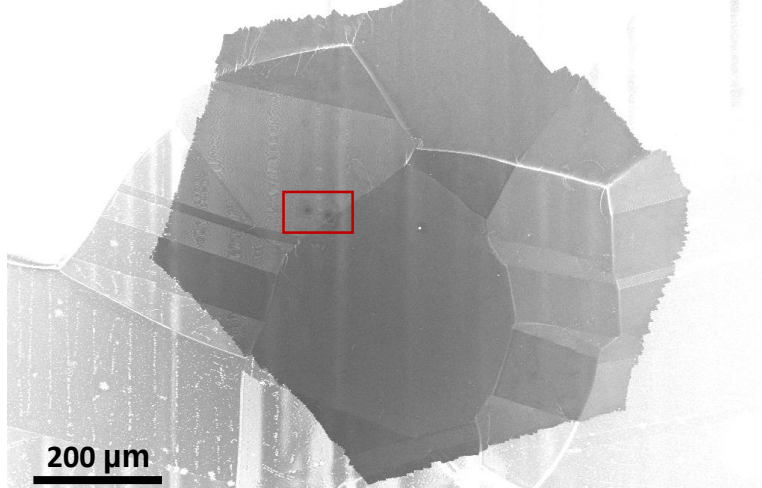


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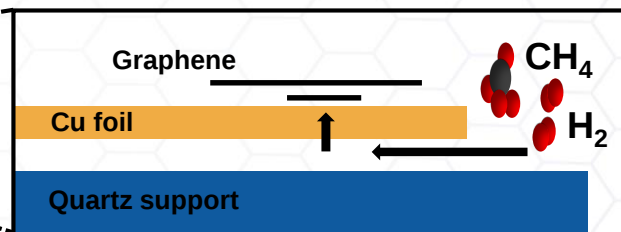
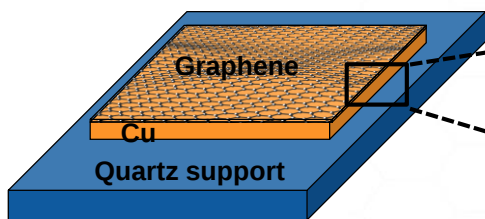
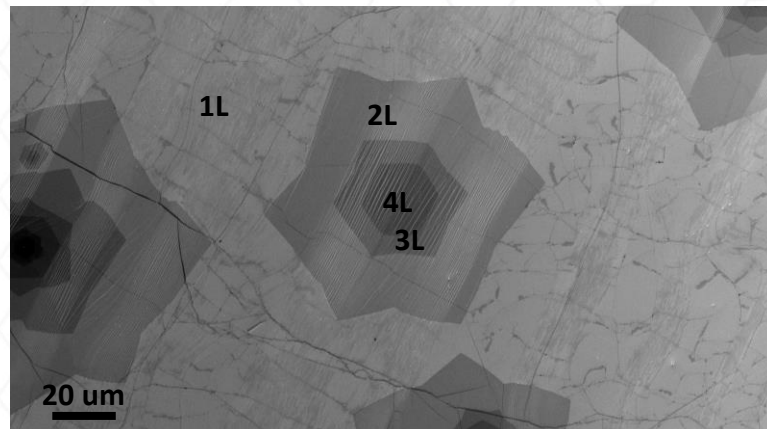
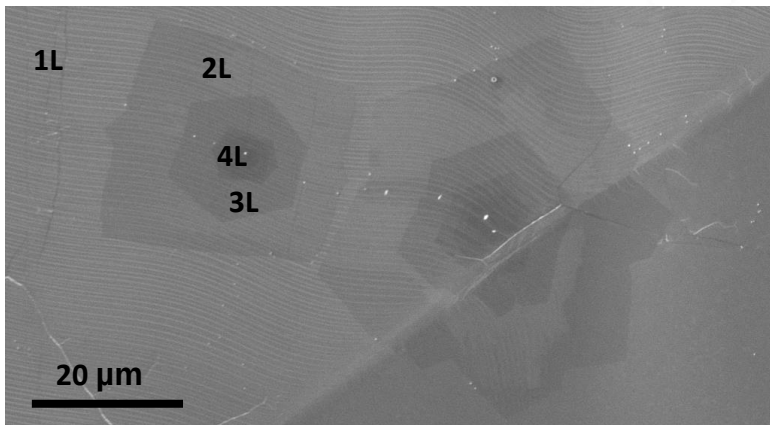
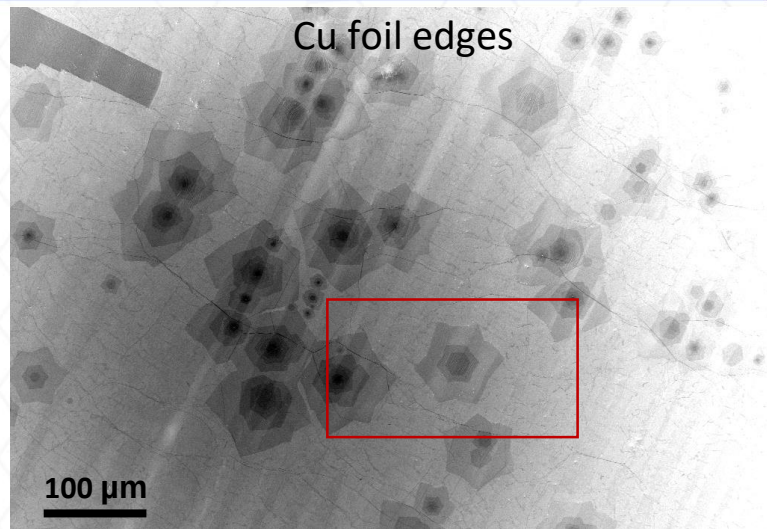


Control over the thickness

Cu foil center

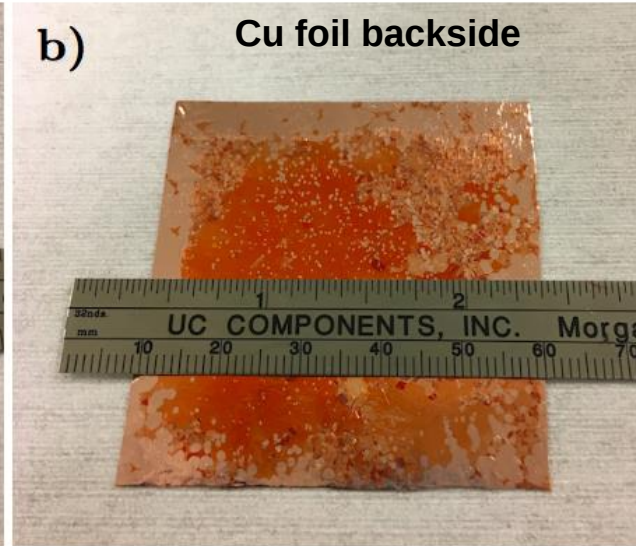
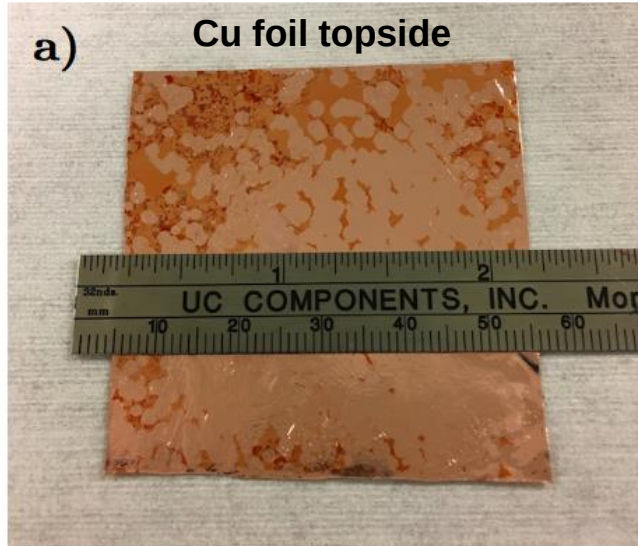


Cu foil edges

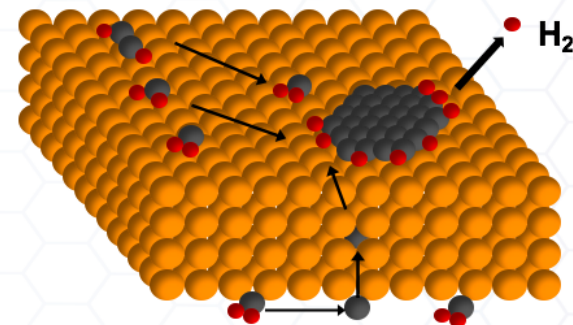
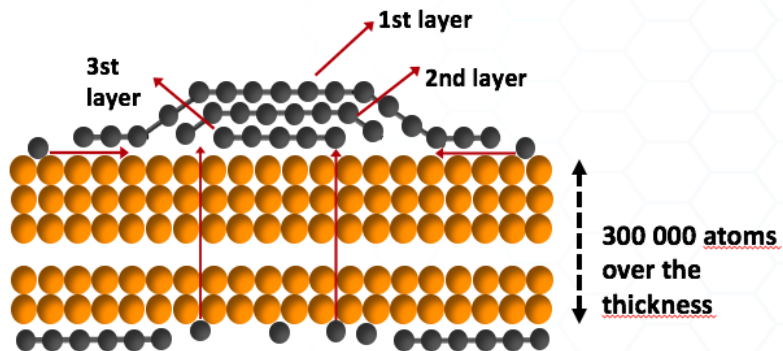


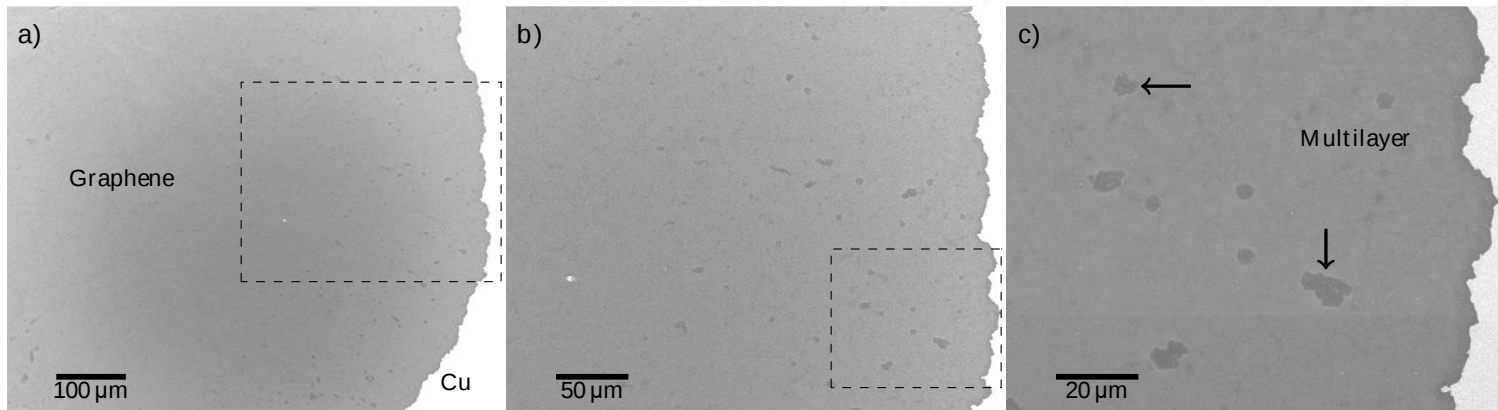
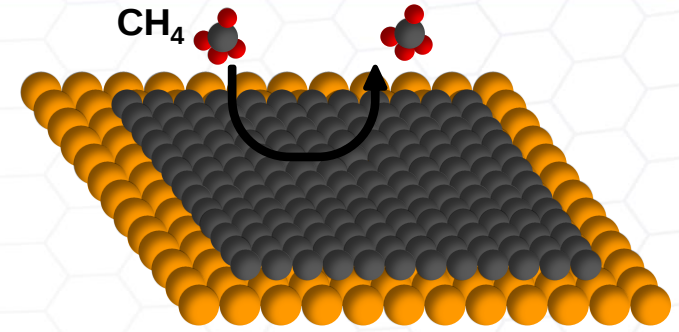
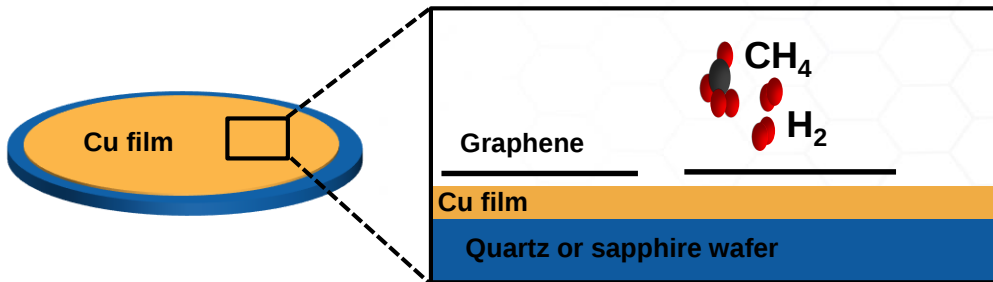


Graphene growth: topside vs. backside

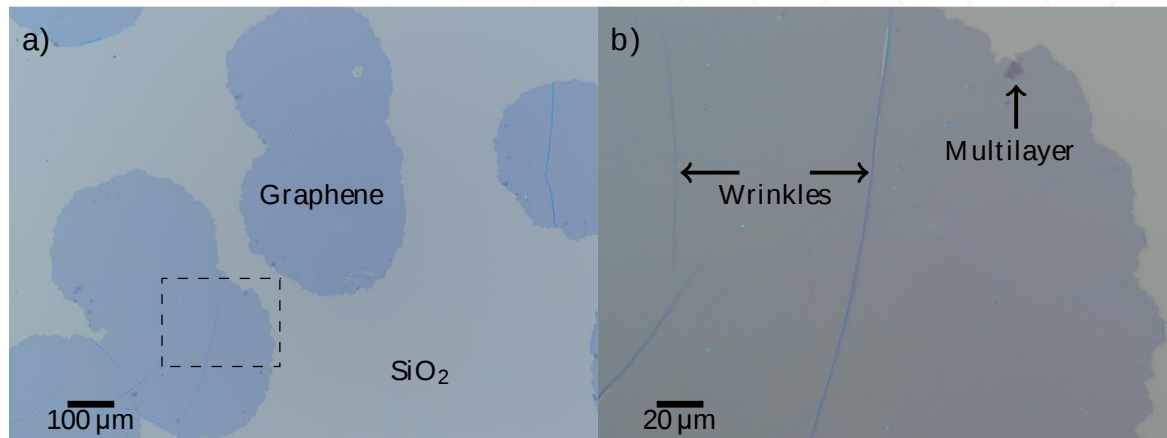


$P_{gr} = 800 \text{ mbar}$
 $T_{gr} = 1050^\circ\text{C}$



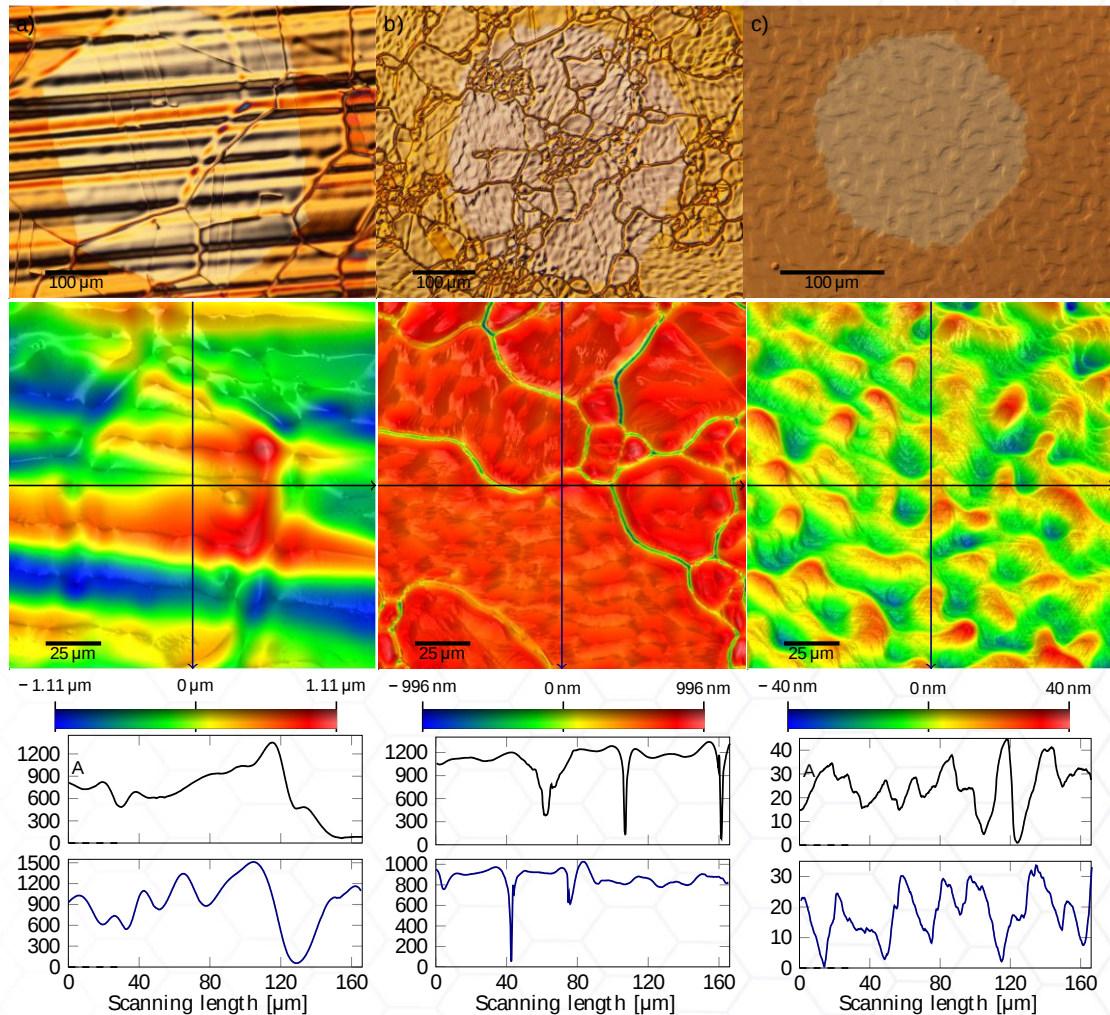
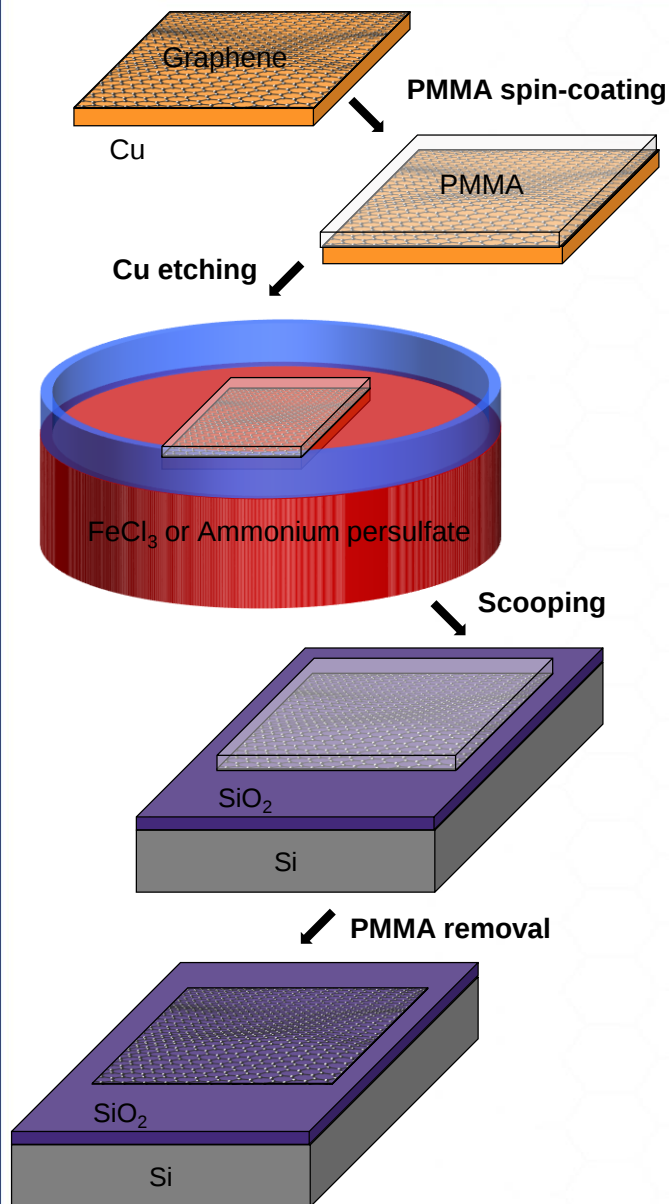


Single layer >99.99%

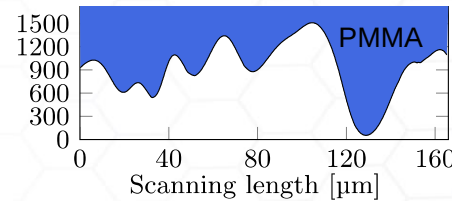
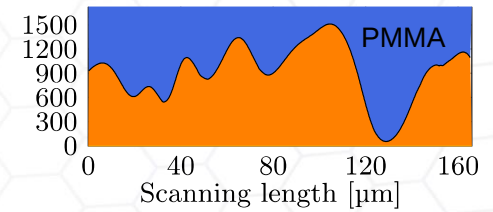
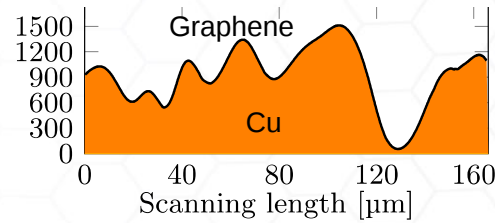
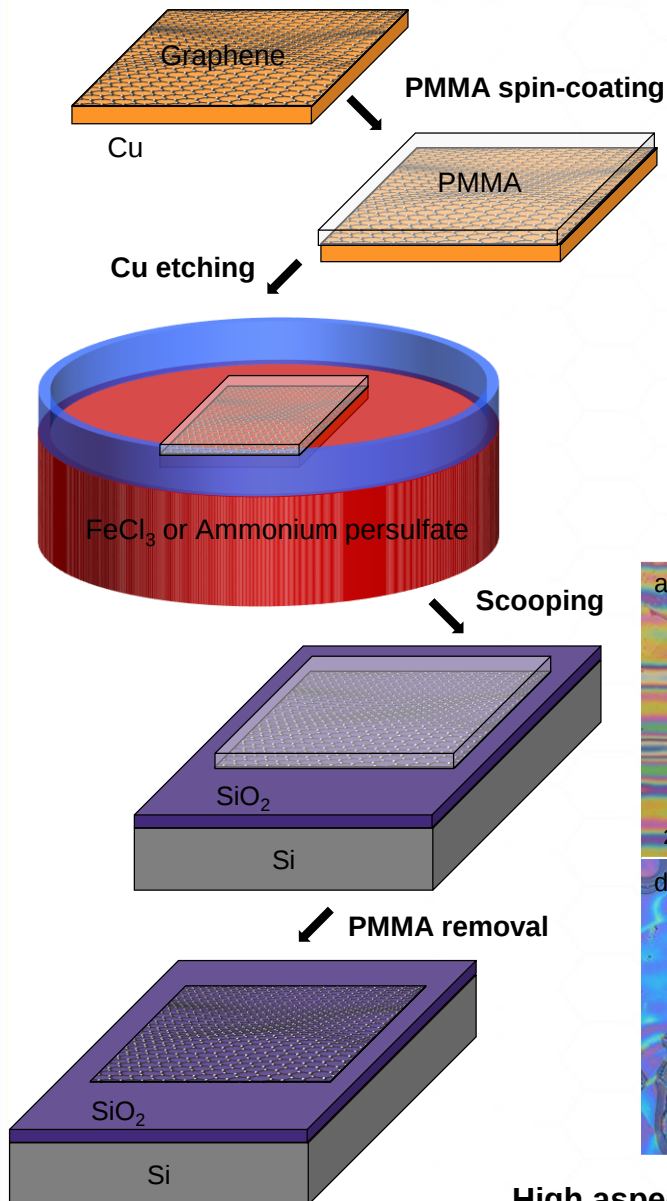




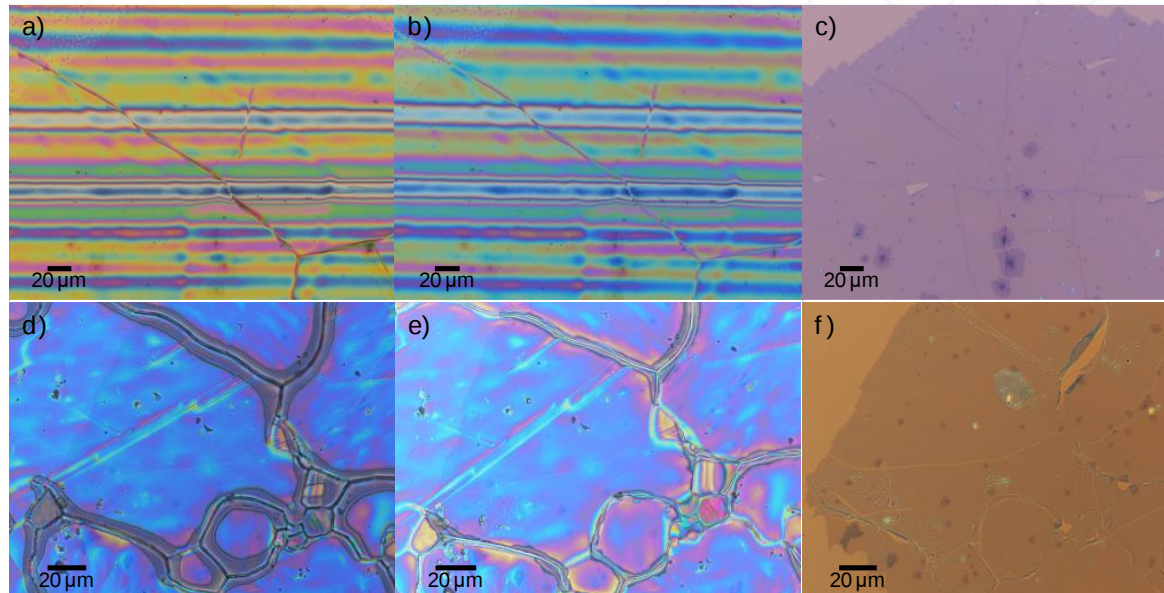
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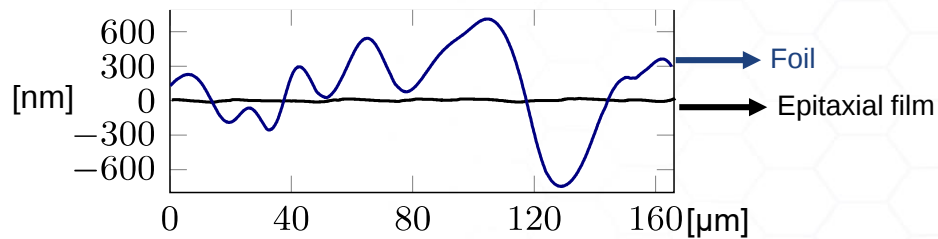
[B. Huet et al., to be submitted]



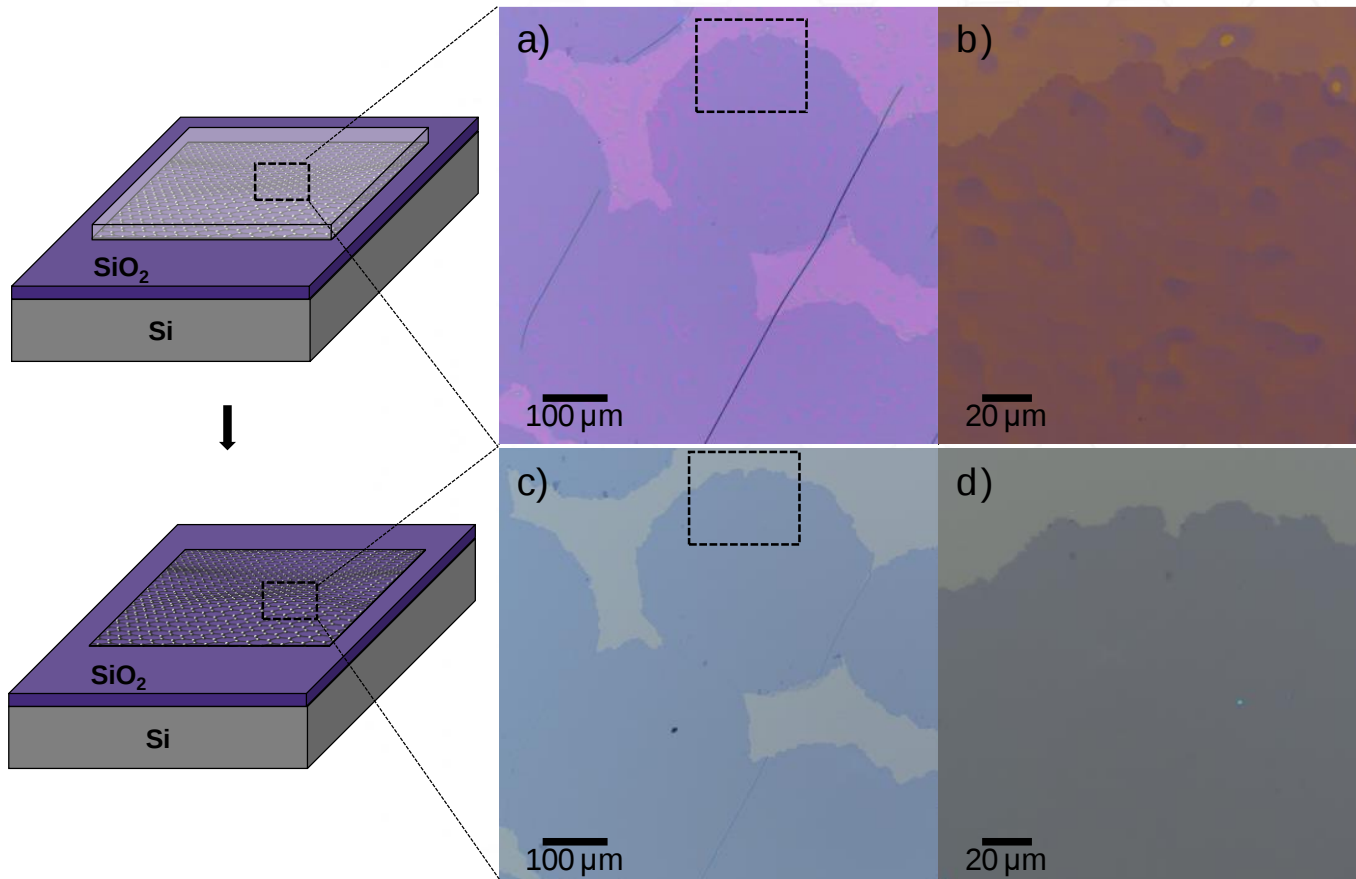
Corrugation/waviness can be partially relaxed!



High aspect ratio Cu features prevent proper contact



Substrate	Excess of surface area
Cu foils	$0.60 \pm 0.45\%$
Polycrystalline Cu films	$1.8 \pm 0.5\%$
Epitaxial Cu films	$0.0105 \pm 0.0021\%$

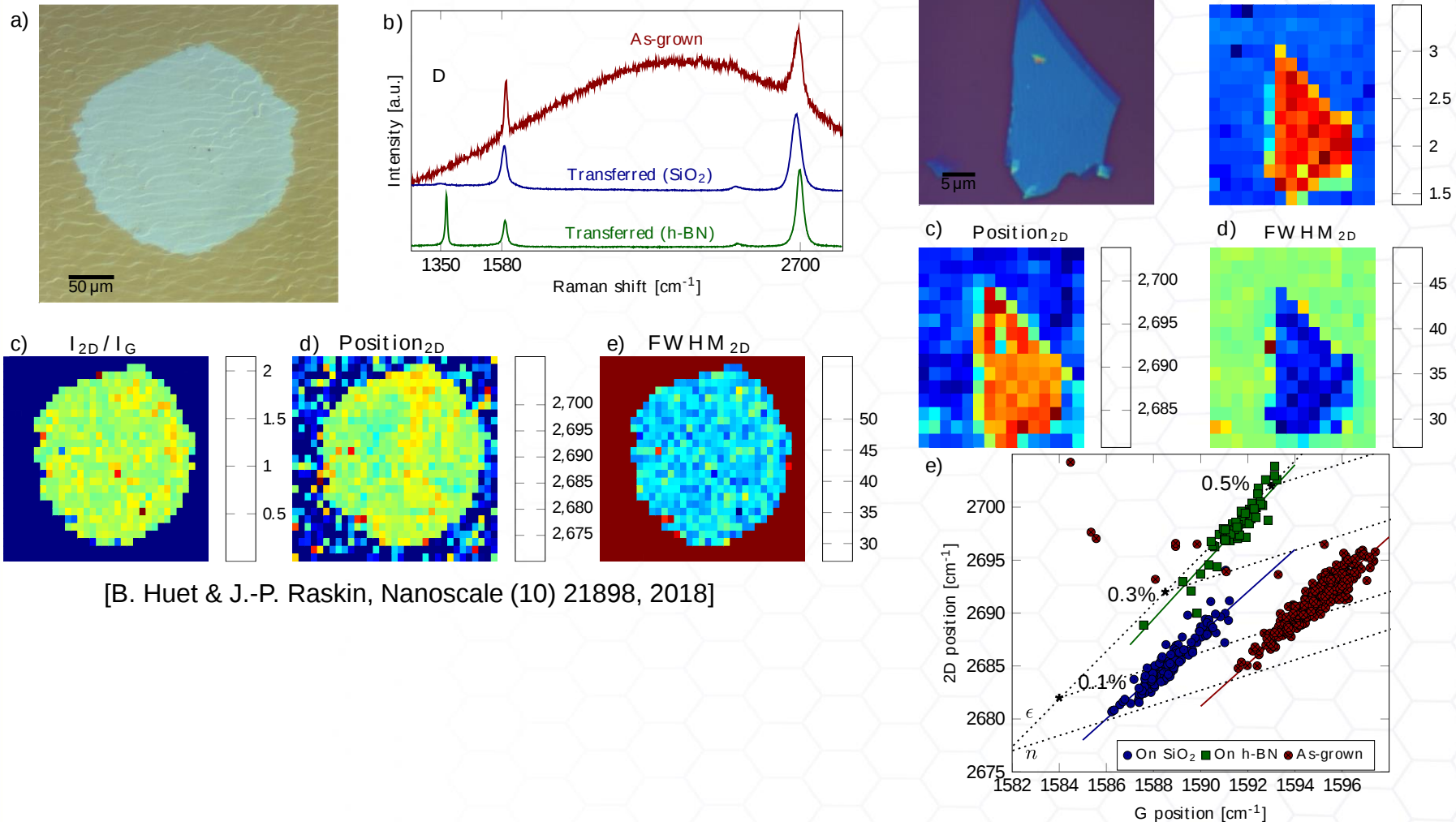




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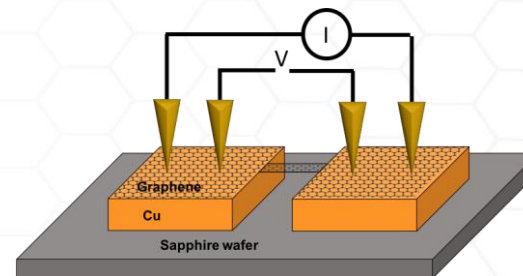
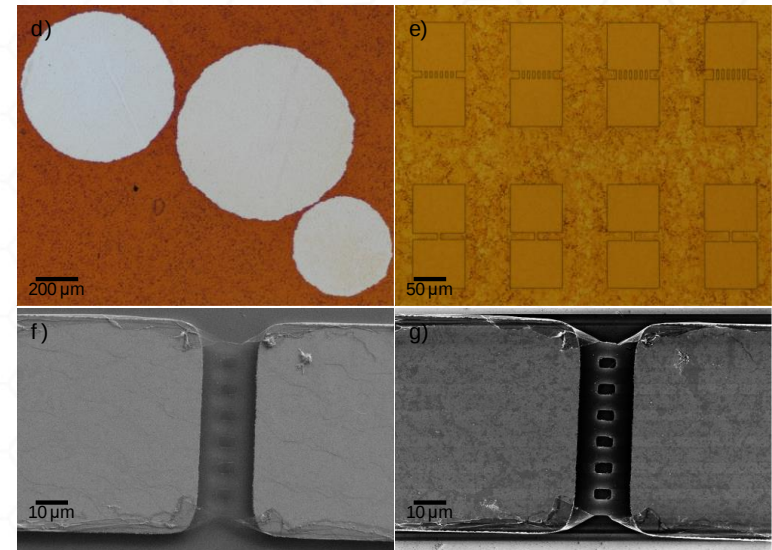
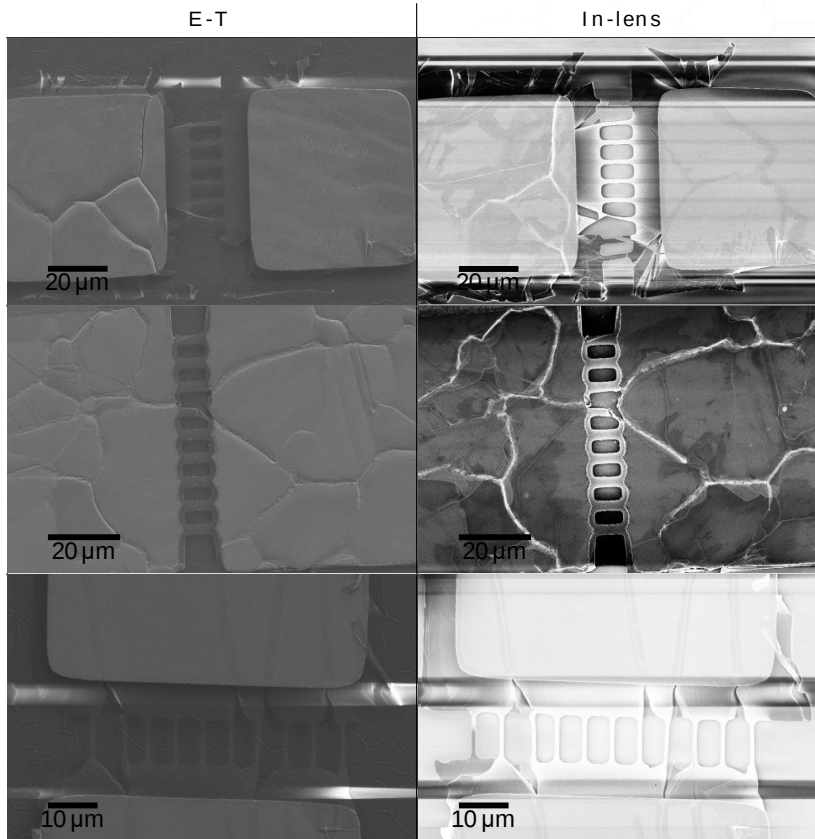
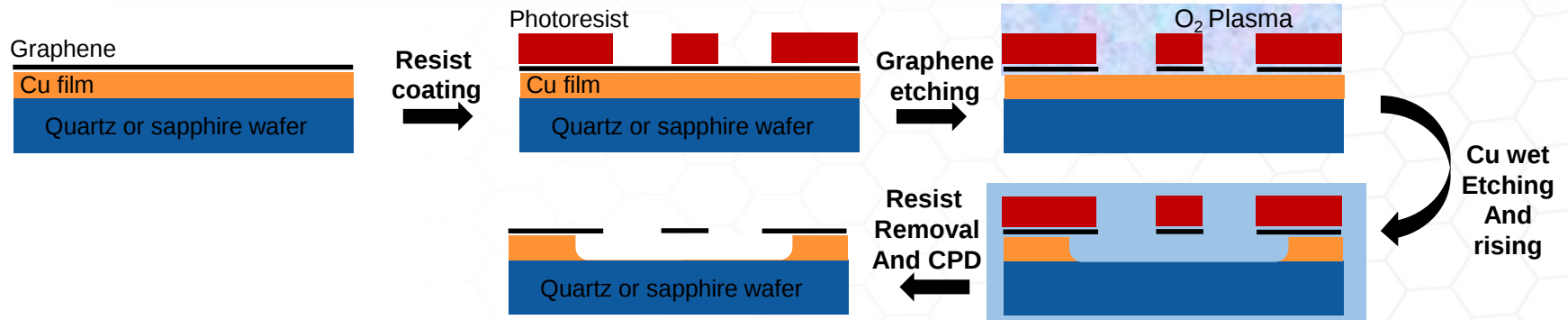
Epitaxial Cu film



[B. Huet & J.-P. Raskin, Nanoscale (10) 21898, 2018]



Direct processing of graphene



The sheet resistance :
 $759 \pm 242 \Omega/\square$

Epitaxial Cu films offer an ideal platform for graphene synthesis, transfer and device fabrication

- Superior surface roughness: about 2 orders of magnitude lower than foils
- Better control over number of layers: suppresses the major mechanism for ad-layer formation
- Improved physical integrity: minimal cracks & wrinkles
- Improved/more reliable transfer
- Direct device fabrication & characterization
- High throughput: batch of >25 wafers (3-in.)

More information:

- B. Huet et al., Role of Cu foil in-situ annealing in controlling the size and thickness of CVD graphene domains, Carbon, 2018.
- B. Huet et al., Role of the Cu substrate in the growth of ultra-flat crack-free highly-crystalline single-layer graphene, Nanoscale, 2018.
- B. Huet et al., Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition, 2D materials, 2019.
- B. Huet et al., Fundamental limitations for the transfer of graphene grown on Cu substrates, to be submitted.



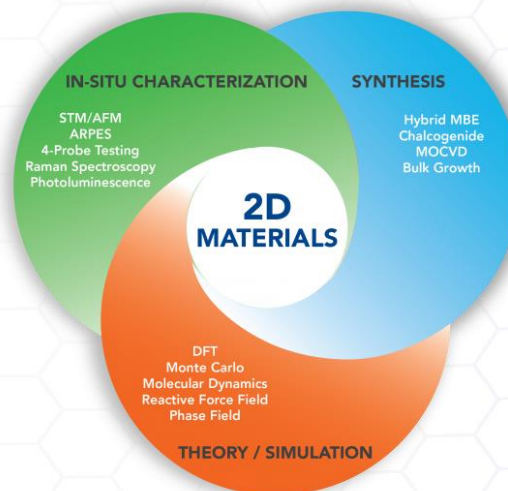
A national user facility focused on advancing the synthesis of graphene and 2D chalcogenides



2D Crystal Consortium
NSF Materials Innovation Platform



PennState



An NSF user facility with broad access:

- Open calls for user proposals,
- No user fees for U.S. academic or government use
- Access to a team of local experts
- Webinars, workshops, website resources
- Partnership opportunities with PUI, MSI